

Technical Data : CD-034

ELECTRO POWER

REP216CH- Power Thyristor**

REP633YS16 - Power Thyristor

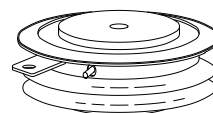
500 - 1600 V_{DRM}; 560 A I_{TAV}

HIGH POWER THYRISTOR FOR INVERTER AND CHOPPER APPLICATIONS

Features:

- . All Diffused Structure
- . Interdigitated Amplifying Gate Configuration
- . Blocking capability up to 1200 volts
- . Guaranteed Maximum Turn-Off Time
- . High dV/dt Capability
- . Pressure Assembled Device

CASE 2T



ELECTRICAL CHARACTERISTICS AND RATINGS

Blocking - Off State

Device Type	V _{RRM} (1)	V _{DRM} (1)	V _{RSM} (1)
R216CH05	500	500	600
R216CH06	600	600	720
R216CH08	800	800	960
R216CH10	1000	1000	1150
R216CH12	1200	1200	1300
R216CH16	1600	1600	1800

V_{RRM} = Repetitive peak reverse voltage

V_{DRM} = Repetitive peak off state voltage

V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I _{RRM} / I _{DRM}	20 mA 40 mA (3)
Critical rate of voltage rise (4)	dV/dt	400 V/μsec

Notes:

All ratings are specified for T_j=25 °C unless otherwise stated.

(1) All voltage ratings are specified for an applied 50Hz/60Hz sinusoidal waveform over the temperature range -40 to +125 °C.

(2) 10 msec. max. pulse width

(3) Maximum value for T_j = 125 °C.

(4) Minimum value for linear and exponential waveshape to 80% rated V_{DRM}. Gate open. T_j = 125 °C.

(5) Non-repetitive value.

(6) The value of di/dt is established in accordance with EIA/NIMA Standard RS-397, Section 5-2-2-6. The value defined would be in addition to that obtained from a snubber circuit, comprising a 0.2 μF capacitor and 20 ohms resistance in parallel with the thyristor under test.

Conducting - on state

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Average on-state current	I _{T(AV)}		560		A	55;æ
Peak one cycle surge (non repetitive) current	I _{TSM}		6300		A	10.0 msec (50Hz), sinusoidal waveshape, 180° conduction, T _j = 125 °C
I square t	I ² t		240000		A ² s	10.0 msec
Latching current	I _L		1000		mA	V _D = 24 V; R _L = 12 ohms
Holding current	I _H		500		mA	V _D = 24 V; I = 2.5 A
Peak on-state voltage	V _{TM}		1.90		V	I _{TM} = 1000 A; Duty cycle ≤ 0.01%
Critical rate of rise of on-state current (5, 6)	di/dt		1000		A/μs	Switching from V _{DRM} ≤ 1000 V, non-repetitive
Critical rate of rise of on-state current (6)	di/dt		500		A/μs	Switching from V _{DRM} ≤ 1000 V

Gating

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Peak gate power dissipation	P _{GM}		200		W	t _p = 40 μs
Average gate power dissipation	P _{G(AV)}		5		W	
Peak gate current	I _{GM}		10		A	
Gate current required to trigger all units	I _{GT}		200		mA	V _D = 6 V; R _L = 3 ohms; T _j = +25 °C
Gate voltage required to trigger all units	V _{GT}		3		V	V _D = 6 V; R _L = 3 ohms; T _j = 25°C
Peak negative voltage	V _{GRM}		5		V	

Dynamic

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Delay time	t _d		1.5	0.7	μs	I _{TM} = 50 A; V _D = Rated V _{DRM} Gate pulse: V _G = 20 V; R _G = 20 ohms; t _r = 0.1 μs; t _p = 20 μs
Turn-off time (with V _R = -50 V)	t _q	20	30		μs	I _{TM} = 500 A; di/dt = 25 A/μs; V _R ≥ -50 V; Re-applied dV/dt = 200 V/μs linear to 80% V _{DRM} ; V _G = 0; T _j = 125 °C; Duty cycle ≥ 0.01%
Reverse recovery charge	Q _{rr}		*		μC	I _{TM} = 500 A; di/dt = 25 A/μs; V _R ≥ -50 V

* For guaranteed max. value, contact facto

THERMAL AND MECHANICAL CHARACTERISTICS AND RATINGS

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Operating temperature	T _j	-40	+125		°C	
Storage temperature	T _{stg}	-40	+150		°C	
Thermal resistance - junction to case	R _{θ(j-c)}	0.045 (1)	0.055 (2)		°C/W	Double sided cooled (1) @ 2000 lb.; (2) @ 800 lb.
Thermal resistance - junction to case	R _{θ(j-c)}	0.090 (1)	0.110 (2)		°C/W	Single sided cooled (1) @ 2000 lb.; (2) @ 800 lb.
Thermal resistance - case to sink	R _{θ(c-s)}		.030 .060		°C/W	Double sided cooled * Single sided cooled *
Mounting force	P	800 3.6	2500 11.1		lb. kN	
Weight	W			2.5 70	oz. g	

* Mounting surfaces

smooth, flat and greased

Note : for case outline and dimensions, see case outline drawing in page 4 of this Technical Data

